

2N4403







PNP General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N4403	*MMBT4403	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$ 40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 0.1 \text{ mA}, I_E = 0$	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 0.1 \text{ A}, I_C = 0$	5.0		V
I _{BEX}	Base Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μА
I _{CEX}	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, V_{BE} = 0.4 \text{ V}$		0.1	μΑ
ON CHAR	RACTERISTICS				
h _{FE}	DC Current Gain	$I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$	30		
		$I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$	60		
		$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100	000	
		$I_C = 150 \text{ mA}, V_{CE} = 2.0 \text{ V}^*$	100 20	300	
	Collector-Emitter Saturation	$I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}^*$ $I_C = 150 \text{ mA}. I_B = 15 \text{ mA}$	20	0.4	V
$V_{CE(sat)}$	Voltage*	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}^*$	0.75	0.95	V
		$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.3	V
SMALL SI	GNAL CHARACTERISTICS				
f⊤	Current Gain - Bandwidth Product	$I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	200		MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 140 kHz			pF
C _{eb}	Emitter-Base Capacitance	$V_{BE} = 0.5 \text{ V}, I_{C} = 0,$ f = 140 kHz		30	pF
h _{ie}	Input Impedance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	_E = 10 V, 1.5		kΩ
h _{re}	Voltage Feedback Ratio	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz) mA, V _{CE} = 10 V, 0.1		x 10 ⁻⁴
h _{fe}	Small-Signal Current Gain	I _C = 1.0 mA, V _{CE} = 10 V, 60 f = 1.0 kHz		500	
h _{oe}	Output Admittance	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	1.0	100	μmho
SWITCHIN	NG CHARACTERISTICS				
t _d	Delay Time	$V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA},$		15	ns
tr	Rise Time	I _{B1} = 15 mA	mA 20		

 $V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA}$

 $I_{B1} = I_{B2} = 15 \text{ mA}$

225

ns

ns

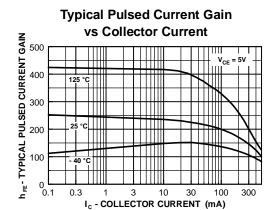
Storage Time

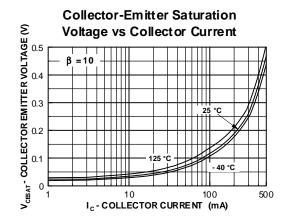
Fall Time

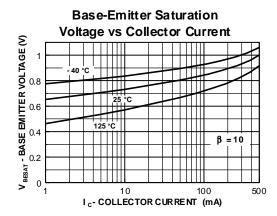
^{*}Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 2.0%

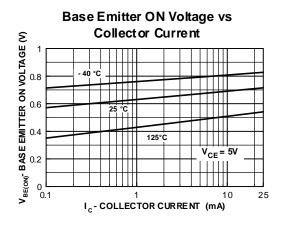
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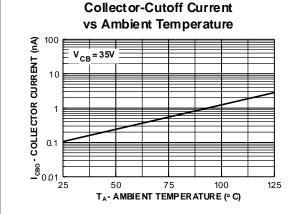
Typical Characteristics

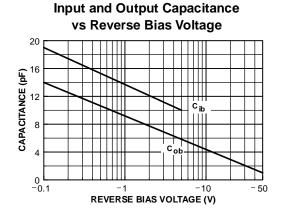








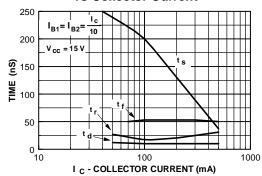




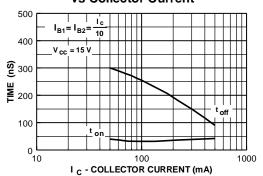
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Typical Characteristics (continued)

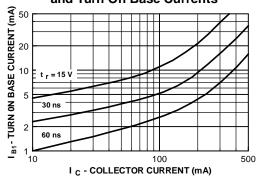
Switching Times vs Collector Current



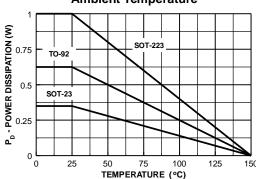
Turn On and Turn Off Times vs Collector Current



Rise Time vs Collector and Turn On Base Currents

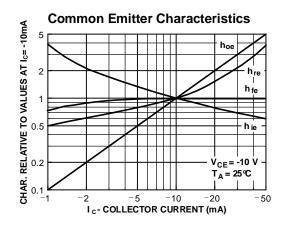


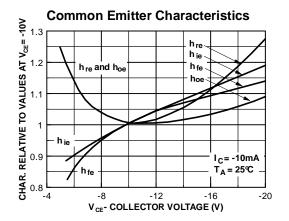
Power Dissipation vs Ambient Temperature

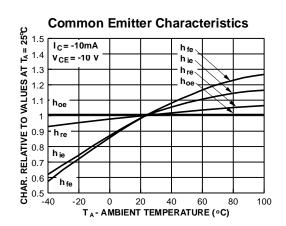


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Typical Common Emitter Characteristics (f = 1.0kHz)







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Test Circuits

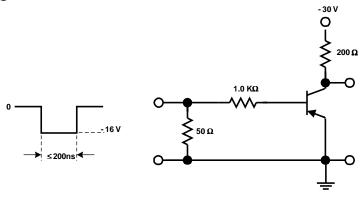


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

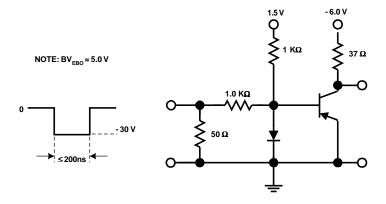


FIGURE 2: Saturated Turn-Off Switching Time Test Circuit

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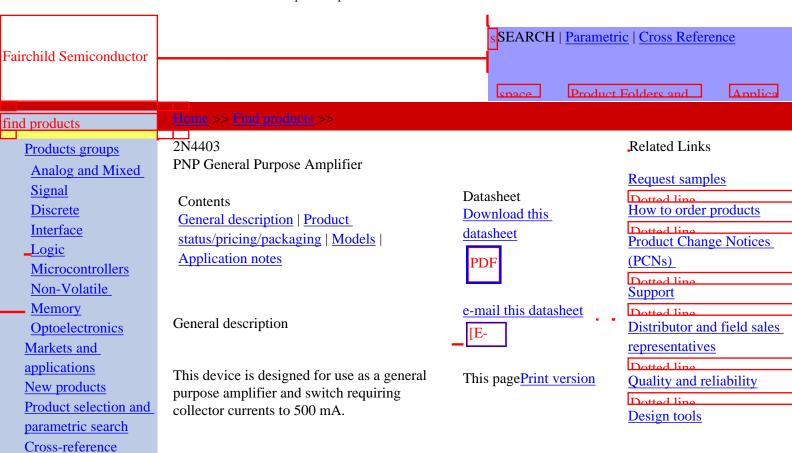
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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition		
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Package marking	Packing method
2N4403BU	Full Production	\$0.05	<u>TO-92</u>	3	N/A	BULK
2N4403TF	Full Production	\$0.05	<u>TO-92</u>	3	N/A	TAPE REEL
2N4403RM	Full Production	\$0.078	TO-92	3	\$Y&3 2N 4403	AMMO
2N4403	Full Production	\$0.078	TO-92	3	\$Y&3 2N 4403	BULK
2N4403TA	Full Production	\$0.05	<u>TO-92</u>	3	N/A	TAPE REEL
2N4403IUTA	Full Production	\$0.05	<u>TO-92</u>	3	N/A	TAPE REEL
2N4403RP	Full Production	\$0.078	TO-92	3	\$Y&3 2N 4403	AMMO
2N4403RA	Full Production	\$0.078	TO-92	3	\$Y&3 2N 4403	TAPE REEL

^{* 1,000} piece Budgetary Pricing

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Models

Package & leads	Condition	Temperature range	Software version	Revision date
PSPICE				
TO-92-3	Electrical	25°C	N/A	N/A

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Application notes

<u>AN-9006: AN-9006 IGBT Application Note for Camera Strobe</u> (146 K) Jul 19, 2002

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